

# **Description**

The HRJE0605JPD uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

# D S

## TO-252-2L

### **General Features**

V<sub>DS</sub> =- 60V, I<sub>D</sub> =-20A

 $R_{DS(ON)} < 72m\Omega @ V_{GS}=-10V$ 

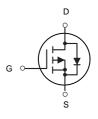
 $R_{DS(ON)}$  < 100m $\Omega$  @  $V_{GS}$ =-4.5V

# **Application**

PWM applications

Load switch

Power management



P-Channel MOSFET

**Package Marking and Ordering Information** 

Product ID	Pack	Brand	Qty(PCS)
HRJE0605JPD	TO252-2L	HXY MOSFET	2500

# ABSOLUTE MAXIMUM RATINGS(TA=25°C unless otherwise noted)

Symbol	Parameter	Limit	Unit
VDS	Drain-Source Voltage	-60	V
VGS	Gate-Source Voltage	±20	V
I <sub>D</sub> (25°C)		-20	Α
I <sub>D</sub> (70°C)	Drain Current-Continuous@ Current-Pulsed (Note 1)	-15	Α
IDM		-48	Α
PD	Maximum Power Dissipation	40	W
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 175	°C
Reja	Thermal Resistance,Junction-to-Ambient (Note 2)	20	°C/W



# **ELECTRICAL CHARACTERISTICS (TA=25** ℃ unless otherwise noted)

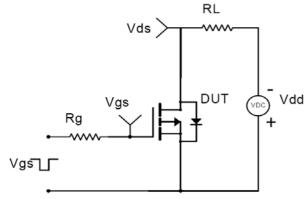
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Drain-Source Breakdown Voltage	BVDSS	V <sub>GS</sub> =0V I <sub>D</sub> =-250μA	-60			V
Zero Gate Voltage Drain Current	loss	V <sub>DS</sub> =-48V,V <sub>GS</sub> =0V			-1	μA
Gate-Body Leakage Current	Igss	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V			±100	nA
Gate Threshold Voltage	V <sub>G</sub> S(th)	Vos=Vgs, lo=-250µA	-1	-1.8	-2.5	V
		VGS=-10V, ID=-10A		64	72	mΩ
Drain-Source On-State Resistance	RDS(ON)	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-10A		90	100	mΩ
Forward Transconductance	grs	V <sub>DS</sub> =-5V,I <sub>D</sub> =-20A	5			S
Input Capacitance	Clss			2460		PF
Output Capacitance	Coss	Coss V <sub>DS</sub> =-30V,V <sub>GS</sub> =0V, F=1.0MHz		220		PF
Reverse Transfer Capacitance	Crss	F=1.0IVII1Z		155		PF
Turn-on Delay Time	td(on)			14		nS
Turn-on Rise Time	t <sub>r</sub>	V <sub>DS</sub> =-30V,V <sub>GS</sub> =-10V,		20		nS
Turn-Off Delay Time	td(off)	- R <sub>GEN</sub> =3Ω I <sub>D</sub> =1A		40		nS
Turn-Off Fall Time	t <sub>f</sub>			19		nS
Total Gate Charge	Qg			48		nC
Gate-Source Charge	Qgs	V <sub>DS</sub> =-30V,I <sub>D</sub> =-20A,V <sub>GS</sub> =-10V		11		nC
Gate-Drain Charge	Qgd			10		nC
Body Diode Reverse Recovery Time	Trr	I <sub>F</sub> =-20A, dI/dt=100A/μs		40		nS
Body Diode Reverse Recovery Charge	Qrr			56		nC
Diode Forward Voltage (Note 3)	Vsp	V <sub>GS</sub> =0V,I <sub>S</sub> =-1A		-0.72	-1	V

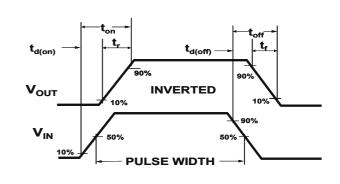
# **NOTES:**

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- Surface Mounted on 1in² FR4 Board, t ≤ 10 sec.
   Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%. 4. Guaranteed by design, not subject to production testing.

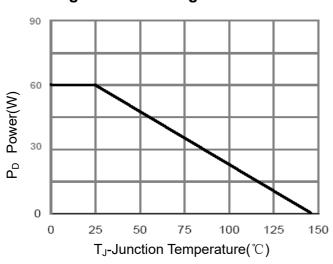


# TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

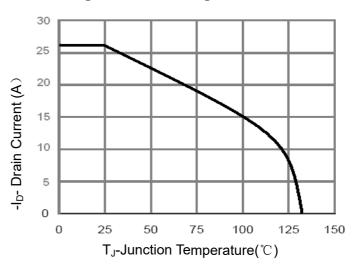




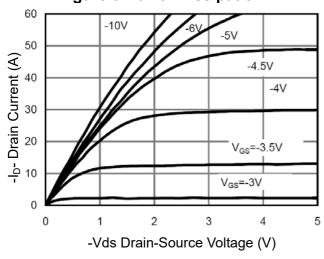
**Figure 1:Switching Test Circuit** 



**Figure 2:Switching Waveforms** 



**Figure 3 Power Dissipation** 



**Figure 4 Drain Current** 

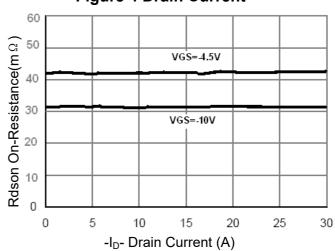
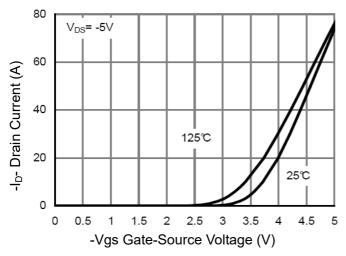


Figure 5 Output CHARACTERISTICS

Figure 6 Drain-Source On-Resistance





**Figure 7 Transfer Characteristics** 

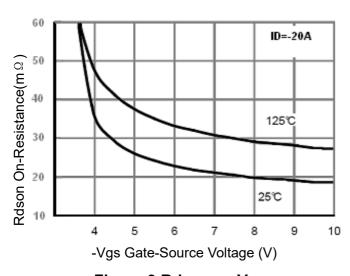


Figure 9 Rdson vs Vgs

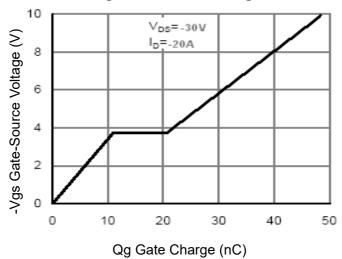


Figure 11 Gate Charge

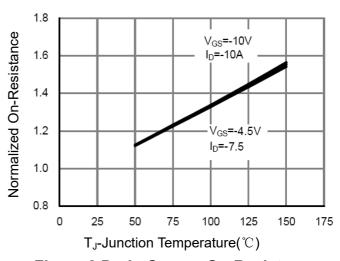


Figure 8 Drain-Source On-Resistance

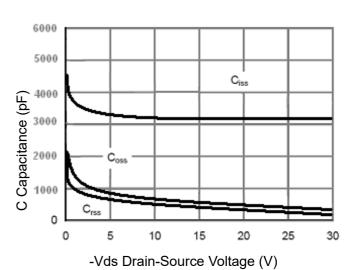


Figure 10 Capacitance vs Vds

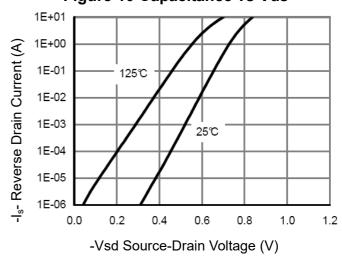


Figure 12 Source- Drain Diode Forward



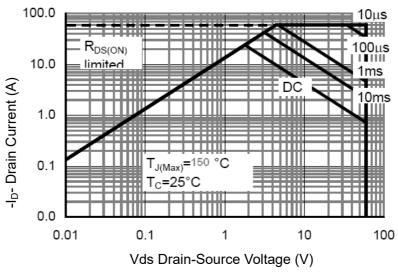


Figure 13 Safe Operation Area

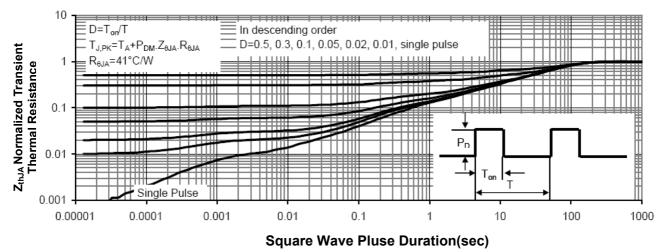
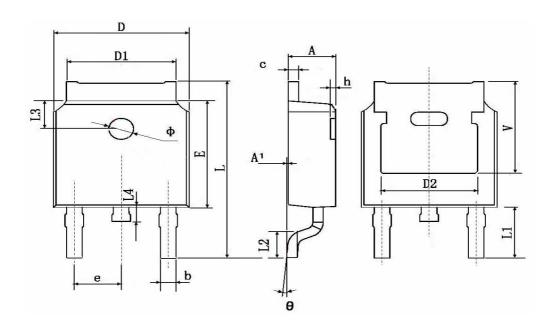


Figure 14 Normalized Maximum Transient Thermal Impedance



# **TO252-2L Package Information**



Symbol	Dimensions In Millimeters		Dimensions In Inches			
	Min.	Max.	Min.	Max.		
A	2.200	2.400	0.087	0.094		
A1	0.000	0.127	0.000	0.005		
b	0.660	0.860	0.026	0.034		
С	0.460	0.580	0.018	0.023		
D	6.500	6.700	0.256	0.264		
D1	5.100	5.460	0.201	0.215		
D2	4.830	4.830 TYP.		0.190 TYP.		
E	6.000	6.200	0.236	0.244		
е	2.186	2.386	0.086	0.094		
L	9.800	10.400	0.386	0.409		
L1	2.90	2.900 TYP.		0.114 TYP.		
L2	1.400	1.700	0.055	0.067		
L3	1.600 TYP.		0.063 TYP.			
L4	0.600	1.000	0.024	0.039		
Ф	1.100	1.300	0.043	0.051		
θ	0°	8°	0°	8°		
h	0.000	0.300	0.000	0.012		
V	5.350 TYP.		0.211 TYP.			

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